Semiconductor designed for harsh conditions

Richardson RFPD, Inc. today announces immediate availability and full design support capabilities for two new laterally diffused metal oxide semiconductor (LDMOS) transistors from Freescale Semiconductor, Inc. (Freescale).

The two highly versatile RF power LDMOS FETs feature enhanced ruggedness of 65:1 VSWR and wideband operation over a broad, 1 MHz to 2 GHz frequency range. The unmatched transistors are capable of delivering full CW rated power over the entire operating frequency range. The combination of integrated stability enhancements and optimized impedances allow for a simpler wideband implementation than previous generations of LDMOS transistors. The devices are housed in Freescale's low thermal resistance packaging and are ideally-suited for applications involving harsh conditions, including HF-UHF transmitters and transceivers, television transmitters, white space data transceivers, aerospace and defense systems, test equipment, and radar systems.

Key features of the 25 W MRFE6VS25NR1 include:

- Frequency range: 1.8 to 2000 MHz
- Gain: 25.4 dB
- Pout: 25 W
- Power added efficiency: 74.5%
- Supply voltage: 50 VDC
- Thermal resistance: 1.2 ºC/W
- Package type: TO-270-2

Key features of the 100 W MRFE6VP100HR5 include:

- Frequency range: 1.8 to 2000 MHz
- Gain: 26 dB
- Pout: 100 W
- Power added efficiency: 70%
- Supply voltage: 50 VDC
- Thermal resistance: 0.38 ºC/W
- Package type: NI-780-4
- Also available in gull wing MRFE6VP100HSR5

The devices are in stock and available for immediate delivery.

RichardsonRFPD
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1-800-737-6937

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